

Specification Amendments

Please amend the specification as indicated hereinafter:

[0035] Referring to Figure 3, Figure 3 is a schematic diagram illustrating a part of the photodiode shown in Figure 2E. The protective layer 228 is silicon nitride and the self-aligned block 224 is silicon oxide and the two layers comprise different refraction indices. As the incident light 300 penetrates the surface of the photodiode sensory region, the incident light 300 is refracted by the protective layer and the self-aligned block, which are of two different refraction indices. The convertibility into photoelectrons of the light absorbed by the photodiode and, after being refracted by the two layers of different refraction indices, is better. In other words, quantum efficiency is higher.